

IN THE CLAIMS

Claim 1-19 (Canceled).

20 (Currently Amended). An integrated circuit comprising:
a semiconductor structure;
a gate formed on said semiconductor structure; and
a P-type source and a P-type drain region, said source and drain regions ~~region~~
including both germanium and a P-type source/drain impurity, said source and drain regions
being strained.

21 (Previously Presented). The circuit of claim 20 wherein the ratio of germanium to
P-type source/drain impurity is greater than one to one.

22 (Previously Presented). The circuit of claim 20 wherein the ratio of germanium to
P-type source/drain impurity is approximately four to one.

23 (Previously Presented). The circuit of claim 20 wherein said source and drain
regions are source and drain extensions.

24 (Original). The circuit of claim 20 wherein said source/drain region that includes both
boron and germanium is a source/drain extension.